

ABSTRACT OF THE DISCLOSURE

The present invention relates to a film forming method of forming an interlayer insulating film having a low dielectric constant for covering wiring. The insulating film covering wiring is formed on a substrate by converting into a plasma and reacting a film forming gas including a component selected from the group consisting of alkoxy compounds having Si-H bonds and siloxanes having Si-H bonds and an oxygen-containing gas selected from a group consisting of O₂, N₂O, NO₂, CO, CO₂, and H₂O.